

Sheet 1 of 1Atty. Docket No.
3442Serial No.: 08/843124
~~not assigned~~**LIST OF REFERENCES CITED BY
APPLICANT****(REVISED FORM PTO-1449)**DATED: April 25, 1997

Applicant: Tomohiro Kawase et al.

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April 25, 1997

Art Unit:

U. S. PATENT DOCUMENTS

*EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	Cl.	Sub- Cl.	File Date
ED	AA 4 9 9 9 0 8 2	3/91	Kremer et al.			

FOREIGN PATENT DOCUMENTS

	DOCUMENT NO.	DATE	COUNTRY	Cl.	Sub- Cl.	Trans.	
						Yes	No
ED	AB 3- 2 5 2 3 9 9	11/ 1991	Japan				
ED	AC 2- 7 4 5 9 7	3/90	Japan				
ED	AD 64 7 9 0 8 7	3/89	Japan				

OTHER DOCUMENTS

ED 6/3/98	AE	Journal of Japanese Association of Crystal Growth, Y. Okabe et al. UNDOPE SEMI-INSULATING GaAs SINGLE CRYSTALS GROWN BY VGF METHOD, Vol. 18, 1991, pages 88 - 95

EXAMINER

Evelyn A. DeLillo

DATE CONSIDERED

Dec 31, 1997

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant